

# Low rDS(on) Small-Signal MOSFETs TMOS Single P-Channel **Field Effect Transistors**

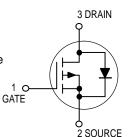
Part of the GreenLine™ Portfolio of devices with energy-conserving traits.

These miniature surface mount MOSFETs utilize Motorola's High Cell Density, HDTMOS process. Low rDS(on) assures minimal power loss and conserves energy, making this device ideal for use in small power management circuitry. Typical applications are dc-dc converters, power management in portable and batterypowered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low rDS(on) Provides Higher Efficiency and Extends Battery Life
- Miniature SOT-23 Surface Mount Package Saves Board Space







## MMBF0202PLT1

Motorola Preferred Device

P-CHANNEL **ENHANCEMENT-MODE TMOS MOSFET**  $r_{DS(on)} = 1.4 \text{ OHM}$ 



#### MAXIMUM RATINGS (T<sub>.</sub>J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>	20	Vdc
Gate-to-Source Voltage — Continuous	VGS	± 20	Vdc
Drain Current — Continuous @ $T_A = 25^{\circ}C$ — Continuous @ $T_A = 70^{\circ}C$ — Pulsed Drain Current ( $t_p \le 10 \mu s$ )	I <sub>D</sub> I <sub>DM</sub>	300 240 750	mAdc
Total Power Dissipation @ T <sub>A</sub> = 25°C <sup>(1)</sup>	PD	225	mW
Operating and Storage Temperature Range	TJ, T <sub>Stg</sub>	- 55 to 150	°C
Thermal Resistance — Junction–to–Ambient	$R_{\theta JA}$	625	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	TL	260	°C

## **DEVICE MARKING**

(1) Mounted on G10/FR4 glass epoxy board using minimum recommended footprint.

### **ORDERING INFORMATION**

Device	Reel Size	Tape Width	Quantity
MMBF0202PLT1	7″	12 mm embossed tape	3000
MMBF0202PLT3	13″	12 mm embossed tape	10,000

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HDTMOS is a trademark of Motorola, Inc. TMOS is a registered trademark of Motorola, Inc.

Thermal Clad is a registered trademark of the Berquist Company.

Preferred devices are Motorola recommended choices for future use and best overall value.

## (Replaces MMBF0202P/D)



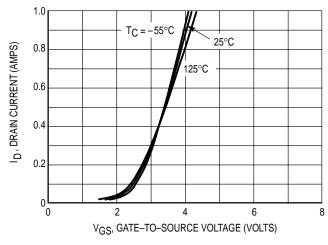
## MMBF0202PLT1

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Char	Symbol	Min	Тур	Max	Unit			
OFF CHARACTERISTICS		•						
Drain–to–Source Breakdown Voltage (V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = 10 μA)		V <sub>(BR)DSS</sub>	20	_	_	Vdc		
Zero Gate Voltage Drain Current (VDS = 16 Vdc, VGS = 0 Vdc) (VDS = 16 Vdc, VGS = 0 Vdc, TJ = 125°C)		$(V_{DS} = 16 \text{ Vdc}, V_{GS} = 0 \text{ Vdc})$		IDSS	_	_	1.0 10	μAdc
Gate-Body Leakage Current (VGS =	± 20 Vdc, V <sub>DS</sub> = 0)	IGSS	_	_	±100	nAdc		
ON CHARACTERISTICS <sup>(1)</sup>		<u> </u>			1			
Gate Threshold Voltage (V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μAdc)		VGS(th)	1.0	1.7	2.4	Vdc		
Static Drain-to-Source On-Resistance (VGS = 10 Vdc, I <sub>D</sub> = 200 mAdc) (VGS = 4.5 Vdc, I <sub>D</sub> = 50 mAdc)		rDS(on)	<u> </u>	0.9 2.0	1.4 3.5	Ohms		
Forward Transconductance (V <sub>DS</sub> =	9FS	_	600	_	mMhos			
DYNAMIC CHARACTERISTICS		•						
Input Capacitance	(V <sub>DS</sub> = 5.0 V)	C <sub>iss</sub>	_	50	_	pF		
Output Capacitance	(V <sub>DS</sub> = 5.0 V)	C <sub>oss</sub>	_	45	_			
Transfer Capacitance	(V <sub>DG</sub> = 5.0 V)	C <sub>rss</sub>	_	20	_			
SWITCHING CHARACTERISTICS <sup>(2)</sup>		•			•	•		
Turn-On Delay Time		<sup>t</sup> d(on)	_	2.5	_	ns		
Rise Time	$(V_{DD} = -15 \text{ Vdc},$	t <sub>r</sub>	_	1.0	_			
Turn-Off Delay Time	R <sub>L</sub> = 75 $\Omega$ , I <sub>D</sub> = 200 mAdc, V <sub>GEN</sub> = -10 V, R <sub>G</sub> = 6.0 $\Omega$ )	t <sub>d</sub> (off)	_	16	_			
Fall Time	1	t <sub>f</sub>	_	8.0	_			
Gate Charge (See Figure 5)	$(V_{DS} = 16 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 200 \text{ mA})$	QT	_	2700	_	рС		
SOURCE-DRAIN DIODE CHARACTE	ERISTICS							
Continuous Current		IS	_	_	0.3	А		
Pulsed Current		ISM	_	_	0.75			
Forward Voltage(2)		V <sub>SD</sub>	_	1.5	_	V		

<sup>(1)</sup> Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
(2) Switching characteristics are independent of operating junction temperature.

## TYPICAL ELECTRICAL CHARACTERISTICS



**Figure 1. Transfer Characteristics** 

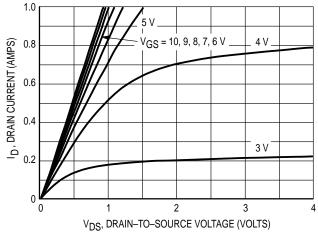


Figure 2. On-Region Characteristics

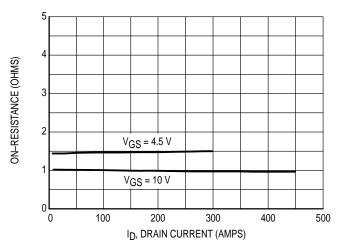


Figure 3. On-Resistance versus Drain Current

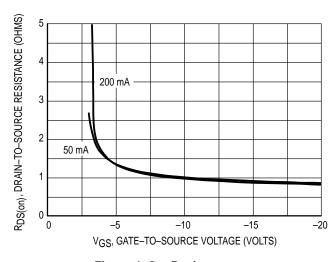


Figure 4. On–Resistance versus Gate–to–Source Voltage

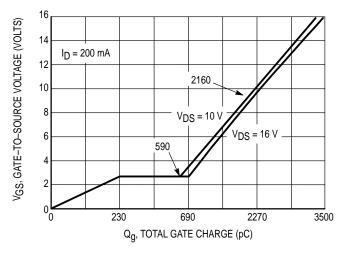


Figure 5. Gate Charge

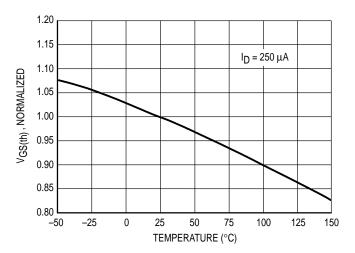
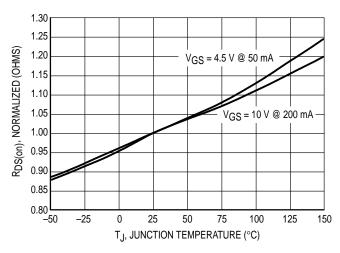


Figure 6. Threshold Voltage Variance Over Temperature

## TYPICAL ELECTRICAL CHARACTERISTICS



140 120 100 C, CAPACITANCE (pF) 80 60  $C_{\text{iss}}$ 40  $C_{oss}$ 20  $C_{rss}$ 0 | 10 15 20  $V_{DS}$ , DRAIN-TO-SOURCE VOLTAGE (VOLTS)

Figure 7. On–Resistance versus Junction Temperature

Figure 8. Capacitance

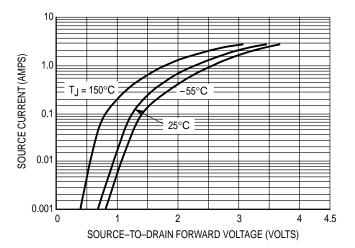
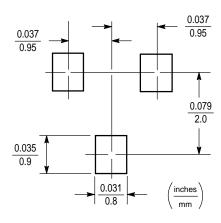


Figure 9. Source-to-Drain Forward Voltage versus Continuous Current (Is)

## INFORMATION FOR USING THE SOT-23 SURFACE MOUNT PACKAGE

## MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



SOT-23

#### SOT-23 POWER DISSIPATION

The power dissipation of the SOT–23 is a function of the drain pad size. This can vary from the minimum pad size for soldering to a pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by  $T_{J(max)}$ , the maximum rated junction temperature of the die,  $R_{\theta JA}$ , the thermal resistance from the device junction to ambient, and the operating temperature,  $T_A$ . Using the values provided on the data sheet for the SOT–23 package,  $P_D$  can be calculated as follows:

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into the equation for an ambient temperature T<sub>A</sub> of 25°C, one can calculate the power dissipation of the device which in this case is 225 milliwatts.

$$P_D = \frac{150^{\circ}C - 25^{\circ}C}{556^{\circ}C/W} = 225 \text{ milliwatts}$$

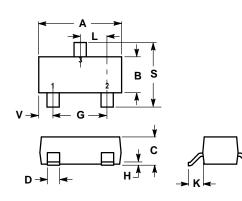
The 556°C/W for the SOT–23 package assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 225 milliwatts. There are other alternatives to achieving higher power dissipation from the SOT–23 package. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad™. Using a board material such as Thermal Clad, an aluminum core board, the power dissipation can be doubled using the same footprint.

#### **SOLDERING PRECAUTIONS**

The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.\*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference shall be a maximum of 10°C.
- The soldering temperature and time shall not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient shall be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes.
   Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling.
- \* Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

#### PACKAGE DIMENSIONS



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  MAXIUMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.1102	0.1197	2.80	3.04	
В	0.0472	0.0551	1.20	1.40	
С	0.0350	0.0440	0.89	1.11	
D	0.0150	0.0200	0.37	0.50	
G	0.0701	0.0807	1.78	2.04	
Н	0.0005	0.0040	0.013	0.100	
J	0.0034	0.0070	0.085	0.177	
K	0.0180	0.0236	0.45	0.60	
L	0.0350	0.0401	0.89	1.02	
S	0.0830	0.0984	2.10	2.50	
٧	0.0177	0.0236	0.45	0.60	

STYLE 21:

PIN 1. GATE

SOURCE

3 DRAIN

**CASE 318-07** SOT-23 (TO-236AB) **ISSUE AD** 

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